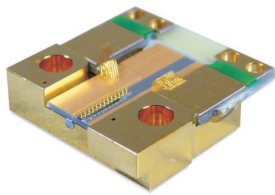


## LU0808Fyyy

808nm Laser Diode on Flat\_mount

**Up to 8W c.w. or 10W in pulsed operation**



### Description:

The LU0808Fyyy series offers an optical power of 8W. Long lifetime is ensured due to the Lumics proprietary laser diode facet passivation technology. This performance makes them a valuable tool for the highly efficient medical laser treatment. Further important applications are micro material processing with exceptional power densities and illumination applications.

### Features & Functions:

- Wavelength 808nm
- Up to 8W c.w. operation
- Up to 10W peak power
- 94µm and 190µm emitter
- Screw holes for mounting
- Mounted on copper base
- Electrically isolated
- Option: FAC lenses mounted

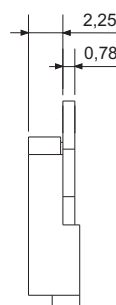
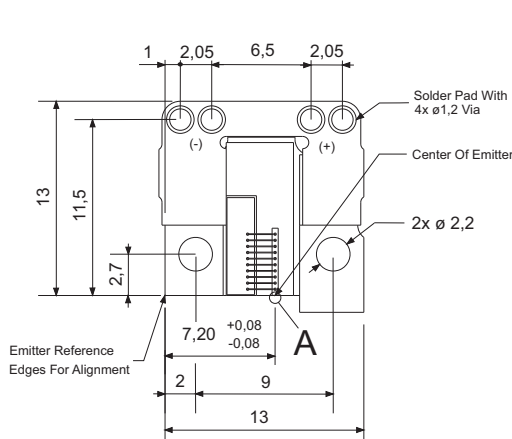
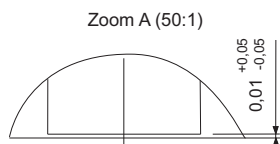
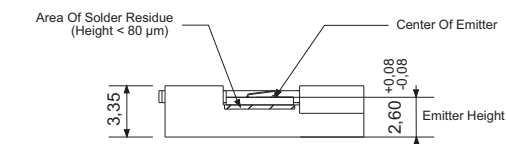
### Benefits:

- Small footprint
- High reliability
- Field proven reliability

### Applications:

- Pumping (SSL)
- Plastic welding
- Illumination
- Medical treatment

### Drawing (dimensions in mm)

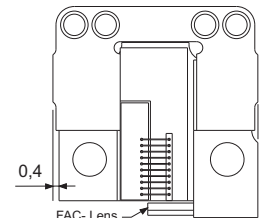


### Connections

Contact Pad	Function
(+)	LD Anode (+)
(-)	LD Cathode (-)

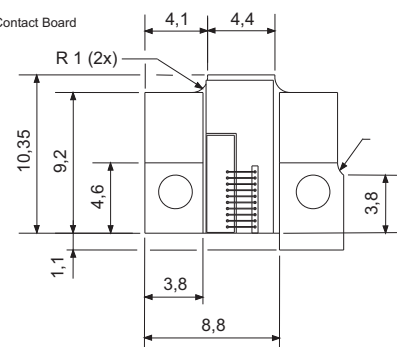
#### Option

Additional FAC-Lens



#### Option

Without Contact Board



**We manufacture diode lasers.**

## Typical Electrical and Optical Characteristics

Parameter	Symbol	LU0808F0047	LU0808F080	Unit
Emitter Width	W	94	190	µm
c.w. Operating Power	P <sub>op (c.w.)</sub>	4.7	8	W
c.w. Operating Current	I <sub>op (c.w.)</sub>	5	9	A
Pulsed (1) Operating Power	P <sub>op (&lt; 30µsec pulse / &lt; 10% d.c.)</sub>	6	10	W
Pulsed (1) Operating Current	I <sub>op (&lt; 30µsec pulse / &lt; 10% d.c.)</sub>	6	12	A
Threshold Current	I <sub>th</sub>	<1	<2	A
Forward Voltage	V <sub>op</sub>	1.8	1.8	V
Slope Efficiency	λ <sub>diff</sub>	1.15	1.15	W / A
Peak Wavelength	λ <sub>peak</sub>	808+/-10	808+/-10	nm
Spectral Width (FWHM)	λ <sub>rWHM</sub>	3	3	nm
Beam Divergence (horizontal) (2)	FWHM, 90% energy inclusion at I <sub>op</sub>	7	7	deg
Beam Divergence (vertical) (2)	FWHM, Gaussian beam at I <sub>op</sub>	25	25	deg
AR Reflectivity (3)	r <sub>f</sub>	1-5	1-5	%
HR Reflectivity	r <sub>r</sub>	95	95	%
Spectral Shift with Temp.	λ <sub>T_Shift</sub>	0.3	0.3	nm / K
Spectral Shift with Current	λ <sub>P_Shift</sub>	0.5	0.5	nm / A
Operating Temp.	T <sub>op</sub>	20 - 30	20 - 30	°C

### Option: FAC lense

Fast axis (vertical) divergence	NA	< 3	< 3	mrad
Vertical width of the beam		< 0.8	< 0.8	mm

### Important Notes:

- (1) Typical pulse condition: pulse <100 µsec / d.c. 5%
- (2) The Intensity I(α,G,SG) of the far field in vertical and horizontal plane versus deflection angle (α) can be approximated with a Zemax Super-Gaussian Diode model by two parameters (first) Gaussian(G) width describing the beam width by the Full Width Half Maximum (FWHM) of the beam intensity in measurement plane and (second) Super Gauss (SG) describing the deviation from a Gaussian shape of the beam whereas:  

$$I(\alpha,G,SG) = \exp(-2((\alpha/G)^2)^{SG})$$
with  $G(FWHM) = FWHM / (2 * \sqrt[SG]{0.346573})$   
Lateral far field: Typical parameter values are SG = 3-4 and G(7°) ~ 6. Due to the non - gaussian shape the FWHM of the beam includes app. 90% of the energy. The beam width increase by current with app. 0.4° / A.  
Vertical far field: Typical parameter values are SG = 1 and G(25°) ~ 21. The beam width does not change by current.
- (3) Other coatings are offered on request

## Absolute Maximum Ratings

Parameter	Symbol	LU0808F047	LU0808F080	Unit
LD c.w. Forward Current	I <sub>op, (c.w.) max</sub>	6	10.5	A
LD pulsed (<30µsec, <5% d.c.) Forward Current	I <sub>op, (pulsed) max</sub>	7	14	A
LD Reverse Voltage	V <sub>R, max</sub>	2	2	V
Maximum Processing Temperatures:				
Solder pads for LD contacts / max 5sec.	T <sub>Op max, solder pad</sub>	250	250	°C
Soldering of Cu base block / max 5sec.	T <sub>Op max, Cu base</sub>	150	150	°C

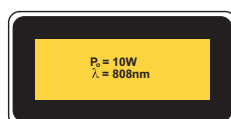
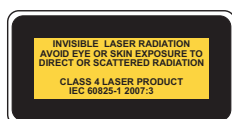
### Notes:

Absolute Maximum Ratings may be applied to the laser module for short period of time only. Exposure to maximum ratings for extended period of time or exposure above one or more max ratings may cause damage or affect the reliability of the device.

Operating Temperature and Rel. Humidity must be chosen such that the dewpoint of humid air around the laser diode is below the operating heat sink temperature to avoid condensing of water on the laser diode facet.

This product contains 1.5% BeO as solid fully metallized ceramic (CAS Number 1304-56-9), 0.05% of solid metallized InAlGaAsP crystal, as well as 0.05% Pb (CAS Nummer 7439-92-1).

## User Safety



**We manufacture diode lasers.**